Product Summary (Typ. @ V_{GS} = 4.5V, T_A = +25°C)

V_{DSS}	$R_{DS(ON)}$	Q_g	Q_{gd}	I_D
8V	35mΩ	9.6nC	0.9nC	4.0A

Description

The DMN1054UCB4 is a Trench MOSFET, engineered to minimize on-state losses and switch ultra-fast, making it ideal for high-efficiency power transfer. Using Chip-Scale Package (CSP) to increase power density by combining low thermal impedance with minimal $R_{DS(ON)}$ per footprint area.

Applications

- DC-DC Converters
- Battery Management
- Load Switch

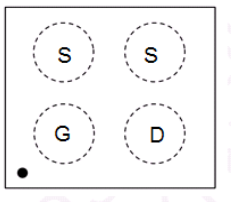
Features

- Trench-CSP Technology with the Lowest on Resistance:
  - $R_{DS(ON)}$ = 35mΩ to Minimize On-State Losses
  - Q_g = 9.6nC for Ultra-Fast Switching
- $V_{GS(TH)}$ = 0.6V Typ. for a Low Turn-On Potential
- CSP with Footprint 0.8mm × 0.8mm
- Height = 0.375mm for Low Profile
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

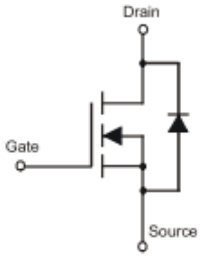
Mechanical Data

- Case: X1-WLB0808-4
- Terminal Connections: See Diagram Below

X1-WLB0808-4



Top-View
Pin Configuration



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN1054UCB4-7	X1-WLB0808-4	3000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

YW = Product Type Marking Code
YM = Date Code Marking
Y or $\overline{Y}$ = Year (ex: D = 2016)
M or $\overline{M}$ = Month (ex: 9 = September)

Date Code Key

Year	2012	2013	2014	2015	2016	2017	2018
Code	Z	A	B	C	D	E	F

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	8	V
Gate-Source Voltage		V_{GSS}	±5	V
Continuous Source Current @ V_{GS} = 4.5V (Note 5)	T_A = +25°C T_A = +70°C	I_D	2.7 2.2	A
Continuous Source Current @ V_{GS} = 4.5V (Note 6)	T_A = +25°C T_A = +70°C	I_D	4.0 3.2	A
Pulsed Drain Current (Pulse duration 10µs, duty cycle ≤1%)		I_{DM}	8	A
Continuous Source-Drain Diode Current		I_S	0.74	A
Pulse Diode Forward Current		I_{SM}	15	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	0.74	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	169	°C/W
Total Power Dissipation (Note 6)	P_D	1.34	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	93	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	8	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1.0	µA	V_{DS} = 8V, V_{GS} = 0V
Gate-Body Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±5V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.35	—	0.7	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	35 38.5 46.4 53.3 64.7	42 50 65 80 110	mΩ	V_{GS} = 4.5V, I_D = 1.0A V_{GS} = 2.5V, I_D = 1.0A V_{GS} = 1.8V, I_D = 0.5A V_{GS} = 1.5V, I_D = 0.2A V_{GS} = 1.2V, I_D = 0.1A
Forward Transfer Admittance	$\|Y_{fs}\|$	—	6.0	—	S	V_{DS} = 6V, I_S = 1.0A
Body Diode Forward Voltage	V_{SD}	—	0.7	1	V	V_{GS} = 0V, I_S = 1.0A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	698	908	pF	V_{DS} = 6V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	—	97	127	pF	
Reverse Transfer Capacitance	C_{rss}	—	90	126	pF	
Gate Resistance	R_g	—	1.3	2.6	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge	Q_g	—	9.6	15	nC	V_{GS} = 4.5V, V_{DS} = 6V, I_D = 1.0A
Gate-Source Charge	Q_{gs}	—	0.9	—	nC	
Gate-Drain Charge	Q_{gd}	—	0.9	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	5.2	10	ns	V_{DD} = 6V, I_D = 1.0A, V_{GEN} = 4.5V, R_G = 1Ω, R_L = 6Ω
Turn-On Rise Time	t_R	—	6.7	14	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	16.6	32	ns	
Turn-Off Fall Time	t_F	—	2	4	ns	
Reverse Recovery Charge	Q_{RR}	—	0.7	1.5	nC	I_F = 1A, di/dt = 100A/µs
Body Diode Reverse Recovery Time	t_{RR}	—	6.9	14	ns	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

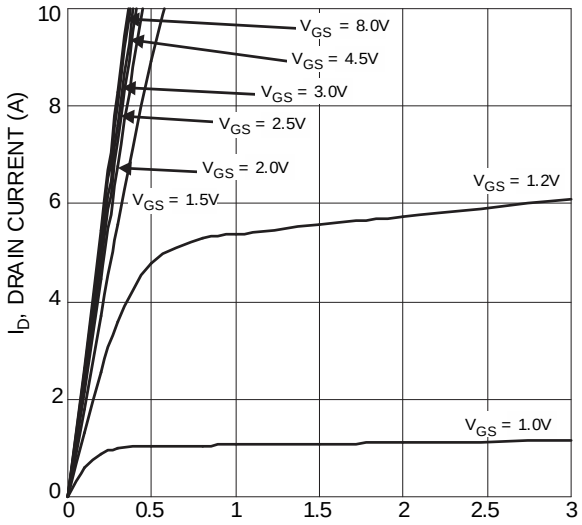


Figure 1 Typical Output Characteristics

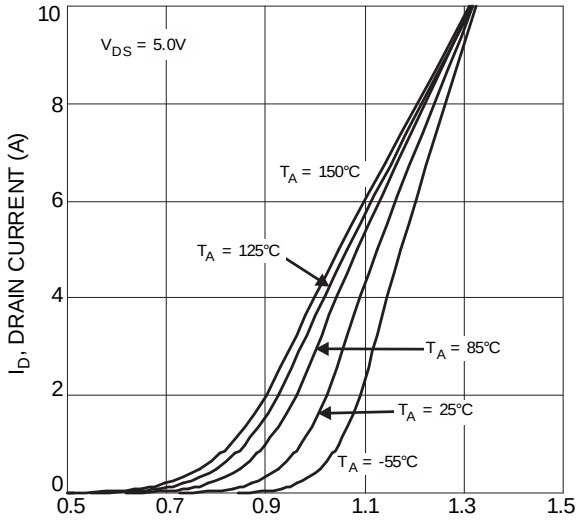


Figure 2 Typical Transfer Characteristics

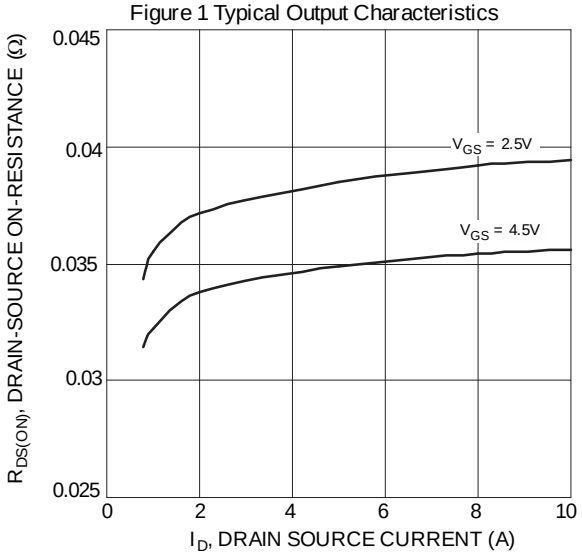


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

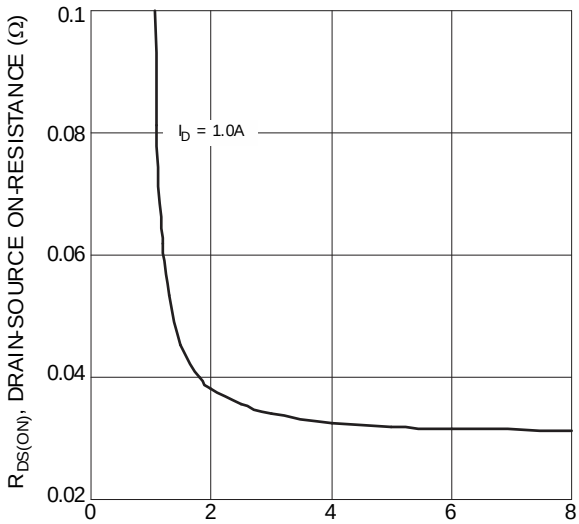


Figure 4 Typical Transfer Characteristic

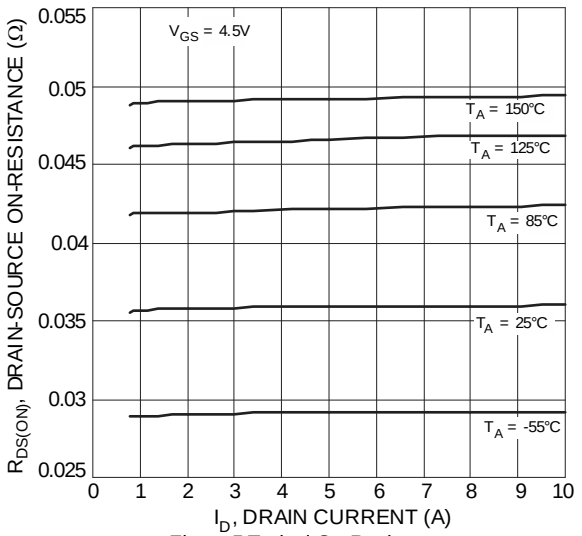


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

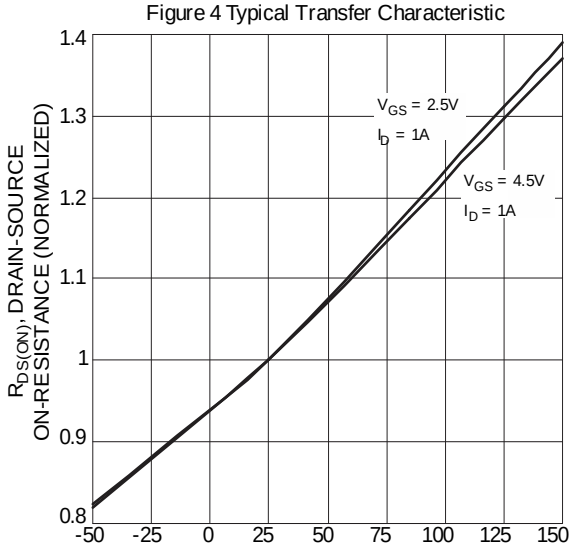


Figure 6 On-Resistance Variation with Temperature

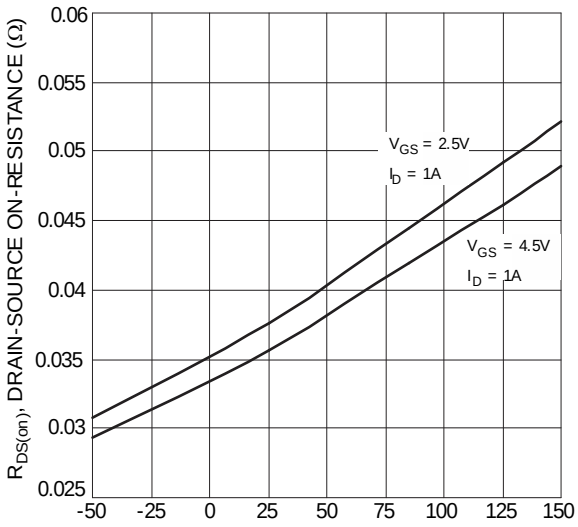


Figure 7 On-Resistance Variation with Temperature

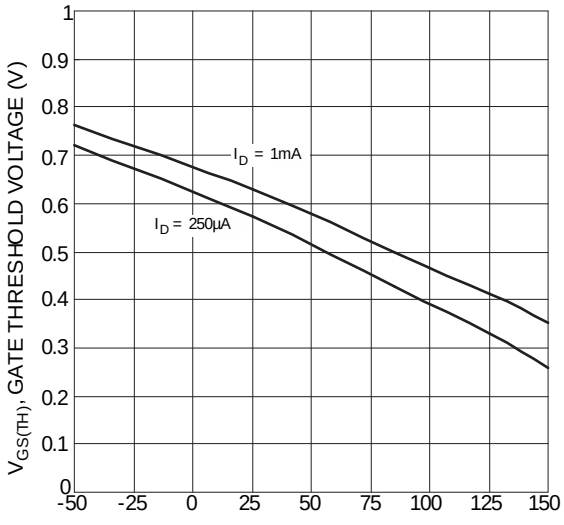


Figure 8 Gate Threshold Variation vs. Ambient Temperature

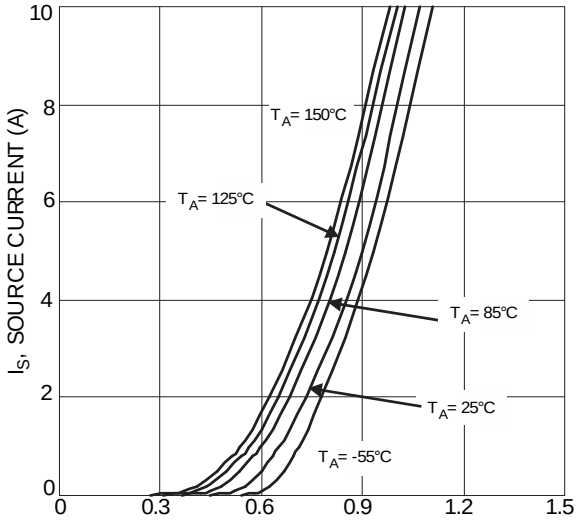


Figure 9 Diode Forward Voltage vs. Current

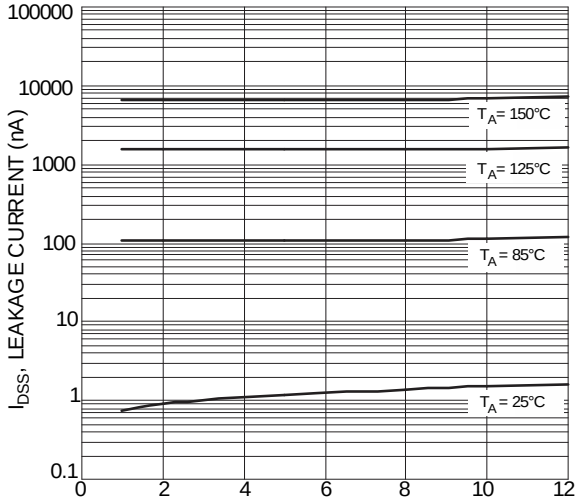


Figure 10 Typical Drain-Source Leakage Current vs. Voltage

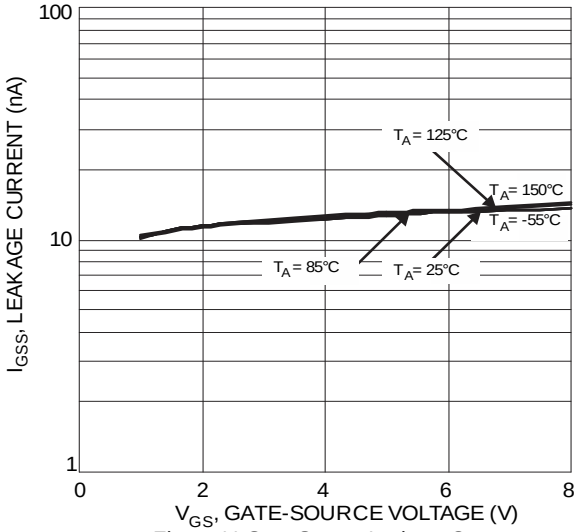


Figure 11 Gate-Source Leakage Current vs. Voltage

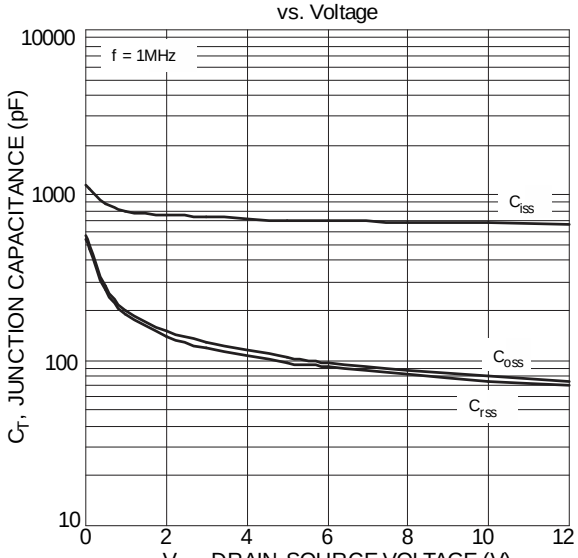


Figure 12 Typical Junction Capacitance

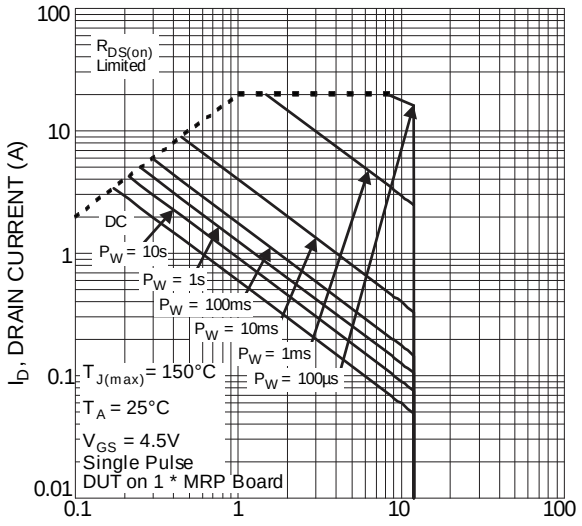


Figure 13 SOA, Safe Operation Area

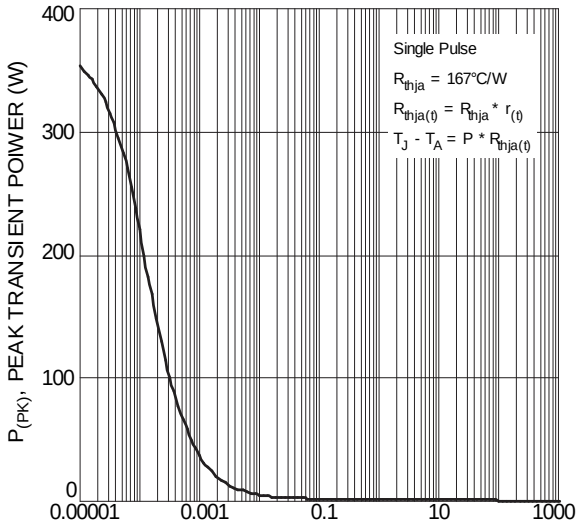


Figure 14 Single Pulse Maximum Power Dissipation

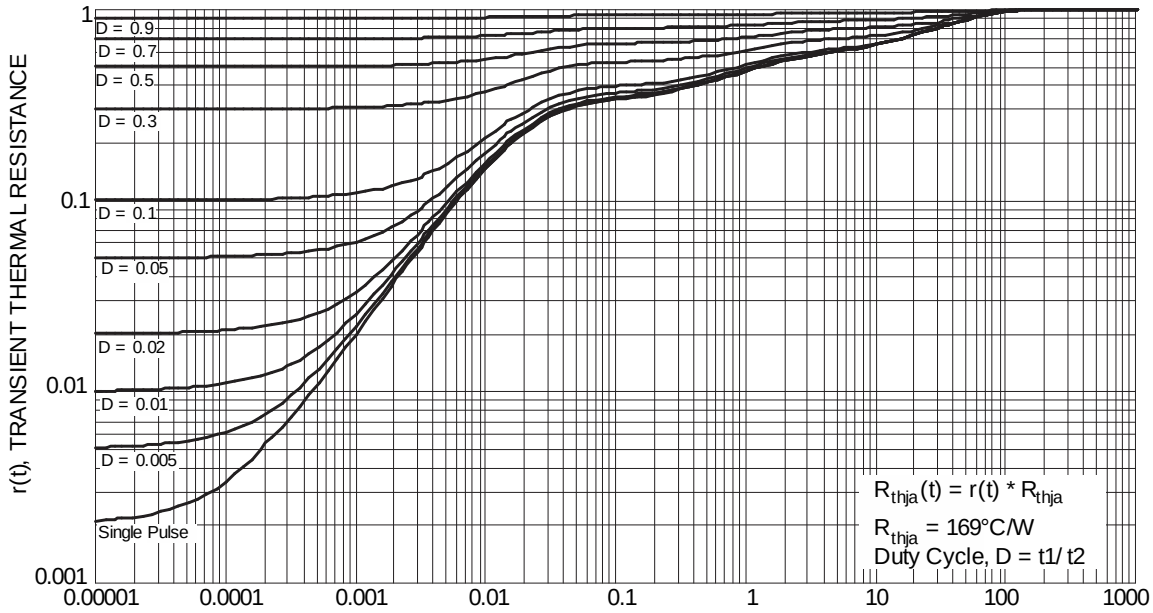
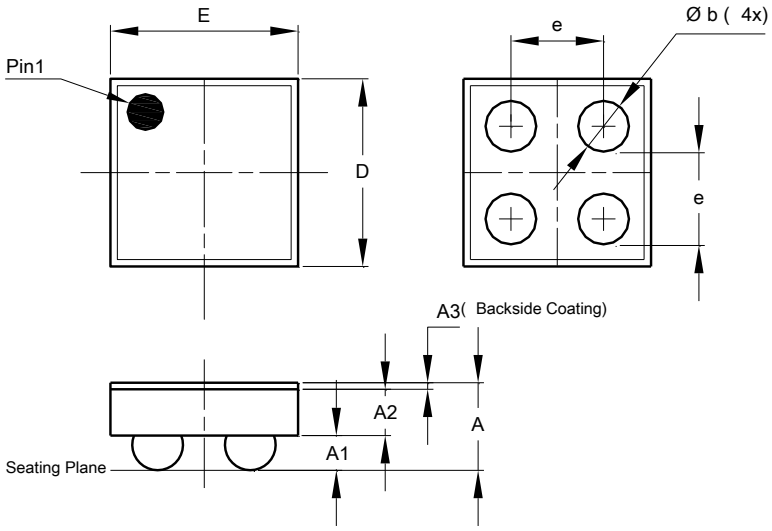


Figure 15 Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X1-WLB0808-4

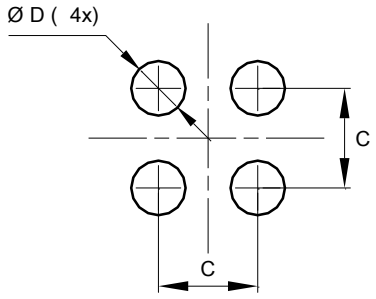


X1-WLB0808-4			
Dim	**Min**	**Max**	**Typ**
A	0.3320	0.4180	0.3750
A1	0.1350	0.1650	0.1500
A2	0.1750	0.2250	0.2000
A3	0.0220	0.0280	0.0250
b	0.1971	0.2409	0.2190
D	0.7900	0.8300	0.8100
E	0.7900	0.8300	0.8100
e	0.400 BSC		
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X1-WLB0808-4



Dimensions	Value (in mm)
C	0.4000
D	0.2190

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